

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S27	1093	((In with doped with GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 15:58
S28	10	("In"?Ga"\$3" with ((superlattice) or (super adj lattice)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/25 23:33
S29	0	("kr 200242311 A")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 16:30
S30	1	("kr 2002042311 A")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 16:30
S31	1	2000KR-0072133.ap.prai.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 16:31
S32	116	epivalley	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 16:32
S33	116	epivalley.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 16:32
S34	0	epivalley.as. and "79659"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 16:32
S35	1	"KR 2002079659 A"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 16:56
S36	1	"KR 2004042311 A"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/13 16:56

S37	11487	"SN"\$1 and cluster	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/14 11:25
S38	10	("In"?"Ga"\$3"N" with ((superlattice) or (super adj lattice)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/17 13:30
S39	0	S37 and S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/14 11:25
S41	38902	"SN"\$1 with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/14 11:25
S42	0	S38 and S41	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/14 11:26
S43	10	("In"?"Ga"\$3"N" with ((superlattice) or (super adj lattice))) and "In"?"Ga"\$3"N"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/14 11:34
S44	6	("In"?"Ga"\$3"N" with ((superlattice) or (super adj lattice))) and ("In"?"Ga"\$3"N" with active)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/14 12:29
S45	2	"6201262".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/14 12:31
S46	10	discrete with crystal with ((silicon adj nitride) or "SN"\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/14 12:32
S50	585	("In"?"Ga"\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/17 16:18
S57	50	("In"?"Ga"\$3"N" with ("0<" or "0≤"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/17 13:37

S58	28	("In"?Ga"\$3" N" with ("0<" or "0s")) same active	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 13:48
S59	10	("In"?Ga"\$3" N" with ("0<" or "0s")) same active same (thickness or angstrom or nm)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 14:43
S60	2	"5393993".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 15:05
S61	35	(aluminum adj indium adj nitride) with buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 14:47
S62	4	"5393993".pn. "5523589".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 15:13
S63	7	"Si" with "In" with "co-doped"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 15:14
S64	1	"Si" with "In" with "co-doped" with contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 15:19
S65	44	SIN with (cluster)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 15:20
S66	2	SIN with (cluster) with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 15:19
S67	0	SIN adj (cluster)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 15:20
S68	44	SIN with (cluster)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 15:20

S69	67	("In"?Ga"\$3"N") with well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 16:00
S70	34	("In"?Ga"\$3"N") with well) and (("In"?Ga"\$3"N") with barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 16:01
S71	0	("In"?Ga"\$3"N") with contact with super	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 16:31
S72	2	("In"?Ga"\$3"N") with super	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 16:18
S73	260	("Ga"\$3"N") with contact with silicon with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 16:32
S74	211	("Ga"\$3"N") with (contact adj layer) with silicon with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 16:33
S75	48	("Ga"\$3"N") adj (contact adj layer) with silicon with doped	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/17 16:33
S76	12	super adj grading	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/25 23:19
S77	1	("In"?Ga"\$3"N" with ((superlattice) or (super adj lattice))) with ("Si" or silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/25 23:28
S78	7	("In"?Ga"\$3"N" with ("Si" or silicon) with doped)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/25 23:31
S79	1	("In"?Ga"\$3"N" with ("Si" or silicon) with doped) same contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/25 23:32

S80	19738	"n-type" with contact with layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/25 23:32
S81	7216	"n-type" with contact with layer with electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/25 23:32
S82	10	("In"?Ga"\$3" N" with ((superlattice) or (super adj lattice)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/25 23:33
S83	1	S82 and S81	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/25 23:33
S84	3	"5929466".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/26 10:55
S85	9147	257/14,94,103,96,97,77,85,79,E33.008, E33.028.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/26 10:56
S86	1098	(In with doped with GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/26 10:56
S87	447	S85 and S86	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/26 10:56
S88	587	("In"?Ga"\$3" N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/26 10:56
S89	30	S85 and S88	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2007/12/26 10:56
S90	9531	257/14,94,103,96,97,77,85,79,E33.008, E33.028.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2008/05/26 00:00

S91	1067	("In"?Ga"\$3"N")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2008/05/26 00:00
S92	3	S90 and S91 and @pd>"20071217"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2008/05/26 00:00
S93	2	("In"?Ga"\$3"N" with ((superlattice) or (super adj lattice))) and @pd>"20071217"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2008/05/26 00:00
S94	0	discrete with crystal with ((silicon adj nitride) or "SiN\$2) and @pd>"20071217"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2008/05/26 00:01
S95	5	S92 S93	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2008/05/26 00:01
S96	1	(nitride and semiconductor and "In" and super and lattice and first and electrode and cluster and active and p-type).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBML_TDB	OR	ON	2008/05/26 00:04

5/26/08 12:05:13 AM

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